



SANYO Semiconductors

DATA SHEET

Monolithic Linear IC

LA5683T — 4ch Switching Regulator Control IC

Overview

The LA5683T is 4ch switching regulator control IC.

Functions

- Low-voltage operation (minimum 1.8V).
- OUT1 and OUT2 can drive external PNP transistors.
- OUT3 and OUT4 can drive external NPN transistors.
- 4-independent-channel standby circuit built-in.
- $\pm 1\%$ accuracy reference voltage.
- Supports MOS transistor drive.
- Channel 2 dead time internally set fixed, duty cycle = 100%.
(The dead time for channels 1, 3, and 4 are set externally.)

Specifications

Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage 1	$V_{CC\text{ max}}$		9	V
Allowable power dissipation	$P_d\text{ max}$	Independent IC	0.4	W
Operating temperature	T_{opr}		-20 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Operating Conditions at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage 1	V_{CC}		1.8 to 8	V
Supply voltage 2	V_{BIAS}		1.8 to 8	V
Output sync current	$I_{SINK\text{ max}}$		0 to 30	mA
Reference voltage output current	I_{REF}		0 to 1	mA
Timing resistor	R_T		3 to 30	k Ω
Timing capacity	C_T		100 to 1000	pF
Triangular wave frequency	f_{OSC}		0.1 to 1	MHz

■ Any and all SANYO Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO Semiconductor representative nearest you before using any SANYO Semiconductor products described or contained herein in such applications.

■ SANYO Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO Semiconductor products described or contained herein.

SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

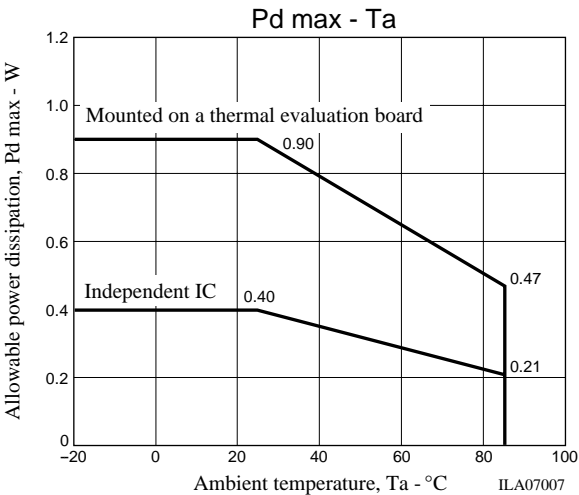
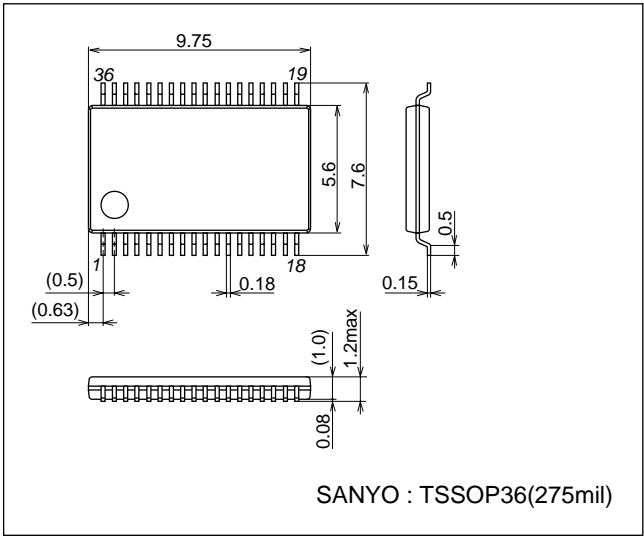
LA5683T

Electrical Characteristics at $T_a = 25^{\circ}\text{C}$, $V_{CC} = V_{STBY1}$ to 4 = 3V, $SCP = 0V$

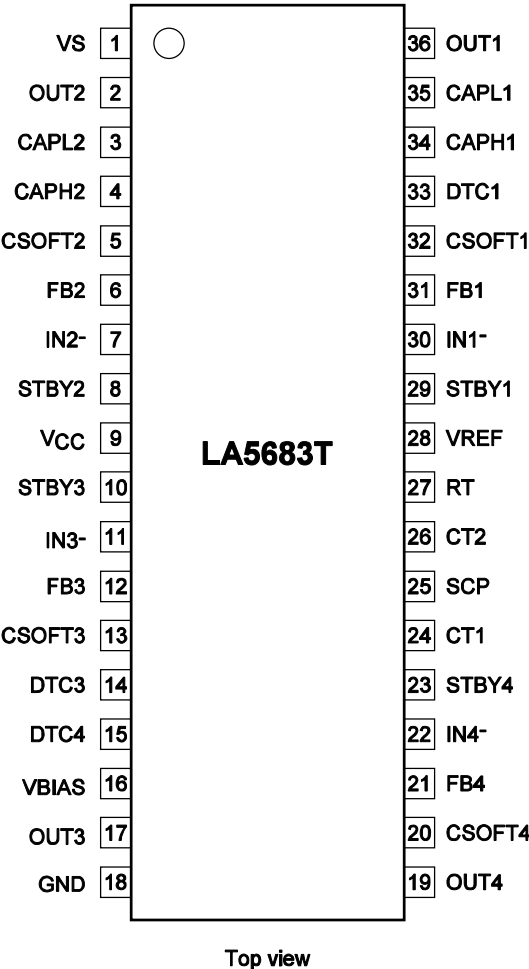
Parameter		Symbol	Conditions	Ratings			Unit
				min	typ	max	
[Error amplifier]							
IN+ pin internal bias voltage		VB	Pins IN1 ⁺ , IN2 ⁺ , IN3 ⁺ , and IN4 ⁺	0.500	0.506	0.512	V
Output L level voltage	CH1 to CH4	V _{Low_FB1}	IN1 ⁻ = 2.0 IFB1 = 20μA			1	V
Output H level voltage	CH1 to CH4	V _{Hi_FB1}	IN1 ⁻ = 0V IFB1 = -20μA	2.25			V
[Protection circuit]							
Threshold voltage		V _{SCP}		1.1	1.25	1.4	V
SCP pin current		I _{SCP}			3.9		μA
[Idle period adjustment block]							
Input bias current		I _{B_DTC}		-15	-3		μA
Threshold voltage 1	CH1	V _{TH1_DTC}	IN1 ⁻ = 0V, duty cycle = 100%	0.67	0.77	0.87	V
Threshold voltage 2	CH1	V _{TH2_DTC}	IN1 ⁻ = 0V, duty cycle = 0%	0.35	0.4	0.45	V
Threshold voltage 3	CH3 to CH4	V _{TH3_DTC}	IN3, IN4 ⁻ = 0V, duty cycle = 100%	0.72	0.8	0.88	V
Threshold voltage 4	CH3 to CH4	V _{TH4_DTC}	IN3, IN4 ⁻ = 0V, duty cycle = 0%	0.4	0.45	0.5	V
[Software start block (CH1 to CH4)]							
Software start current	CH1 to CH4	I _{SF}	CSOFT = 0V	3.16	3.95	4.74	μA
Software start resistance	CH1 to CH4	R _{SF}		160	200	240	kΩ
[Output blocks 1 and 2 (CH1 and CH2)]							
OUT pin source current		I _{OUT12_SOUR}	IN1, 2 ⁻ = 0V DTC1 = 0V V _{OUT1, 2} = 2.7V ICAPH = 0.5mA	10			mA
OUT pin sink current		I _{OUT12_SINK}	IN1, 2 ⁻ = 0V DTC1 = 1.0V V _{OUT1, 2} = 2.3V	35	45	55	mA
[Output blocks and 4 (CH3 and CH4)]							
OUT pin source current		I _{OUT34_SOUR}	V _{OUT3, 4} = 0.9V DTC3, 4 = 1.0V IN3, 4 = 0V	20	30	40	mA
OUT pin sink current		I _{OUT34_SINK}	V _{OUT3, 4} = 0.3V DTC3, 4 = 1.0V IN3, 4 = 1.0V	30			mA
OUT pin high level voltage		V _{OUT34_Hi}	I _{OUT3, 4} = -10mA DTC3, 4 = 1.0V IN3, 4 = 0V	2			V
OUT pin low level voltage		V _{OUT34_Low}	I _{OUT3, 4} = 10mA DTC3, 4 = 0V IN3, 4 = 1.0V			0.2	V
[Triangular wave form generator block]							
Current setting pin voltage		VT_RT	RT = 5.6kΩ	1.190	1.260	1.330	V
Output current		I _{OH_CT}	VCT = 0.5V, RT = 5.6kΩ		230		μA
Output current ratio		ΔI _{O_CT}		0.8	1.0	1.2	
Oscillation frequency		f _{OSC1}		380	440	500	kHz
[Reference voltage block]							
Reference voltage		VREF	I _{REF} = -1mA	1.244	1.257	1.270	V
Line regulation		V _{LN_REF}	V _{CC} = 1.8V to 8V			10	mV
Load regulation		V _{LD_REF}	I _{REF} = -0.1mA to -1mA			10	mV
[STBY circuit]							
On voltage		V _{ON_STBY}		1.15			V
Off voltage		V _{OFF_STBY}				0.2	V
Pin input current		I _{IN_STBY}	VSTBY1 to 4 = 3V			70	μA
[All circuits]							
Operating-time current drain		I _{CC1}	FB1, 2, 3, 4 = 1.5V DTC1, 3, 4 = 1.5V		15	18	mA
Standby-time current drain		I _{CC2}	VSTBY1 to 3 = 0V			1	μA

Package Dimensions

unit : mm
3253B

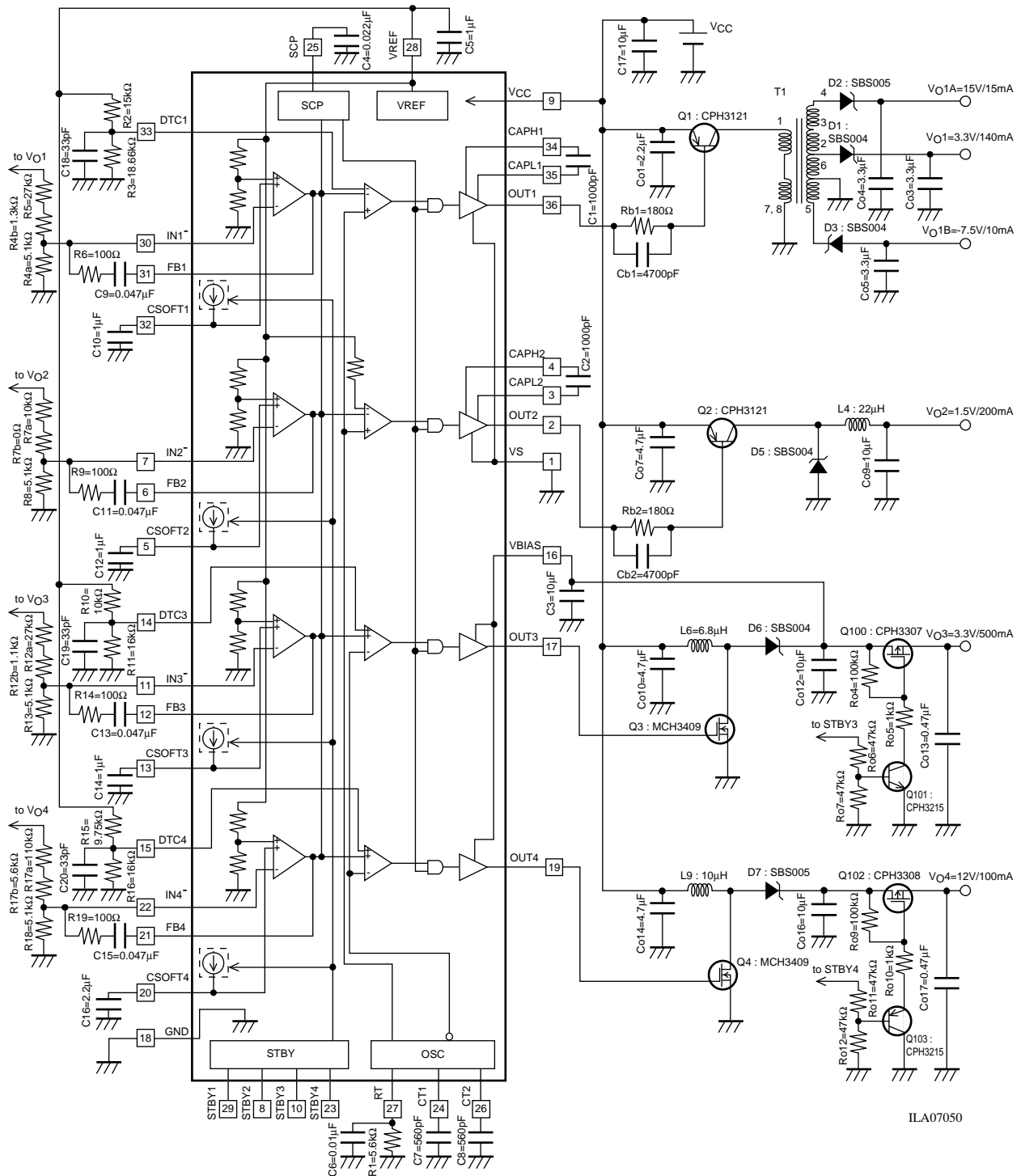


Pin Assignment



Block Diagram and Application Circuit Examples 1

2-dry-battery (1.8V to 3.2V) configuration



T1 = Sumida product

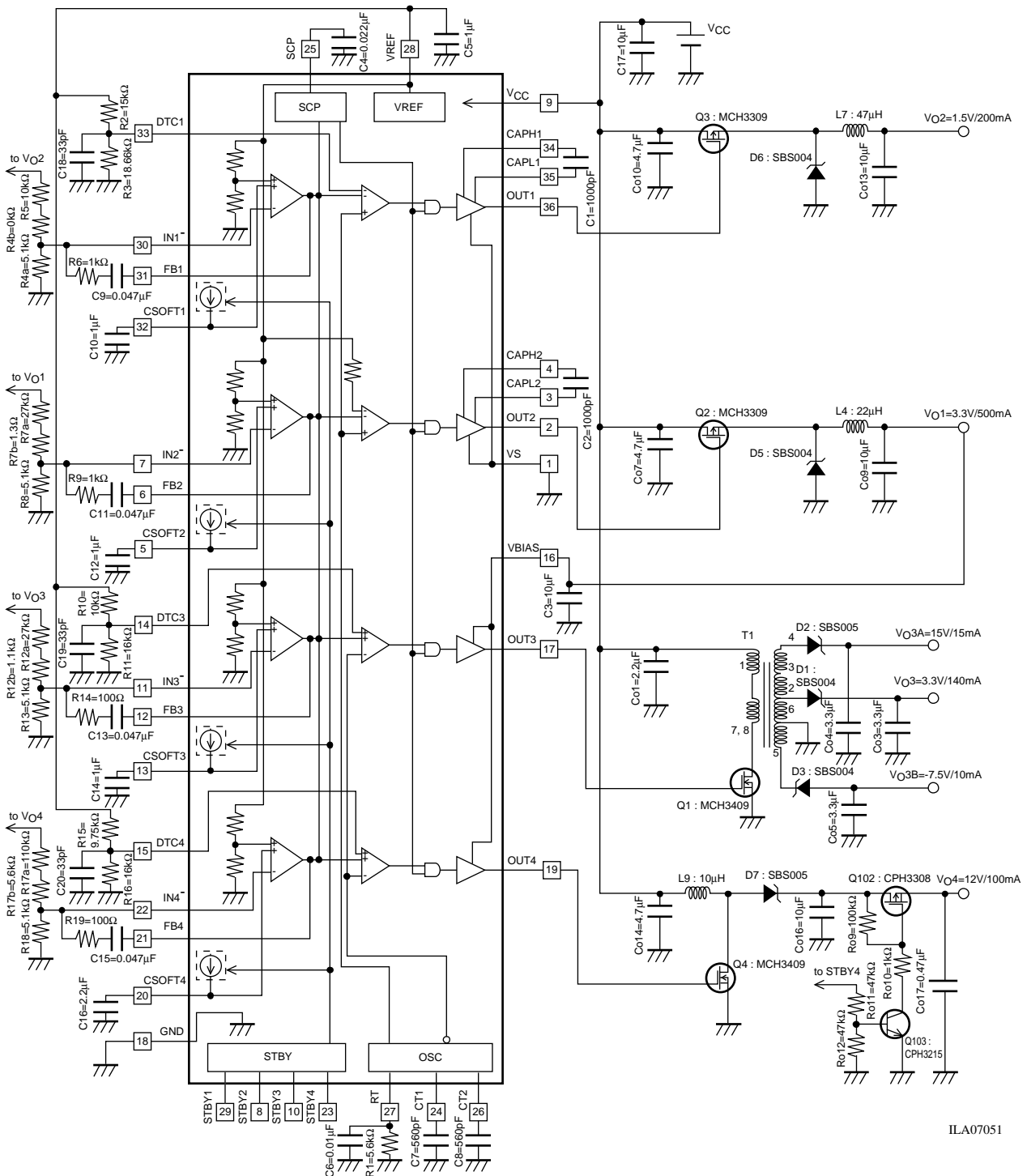
L4 = TDK product: RLF5018-220MR63

L6 = TDK product: SLF6028-6R8M1R5

L9 = Toko product: 636CY-100M

Application Circuit Examples 2

4-dry battery (3.5V to 6.5V) configuration

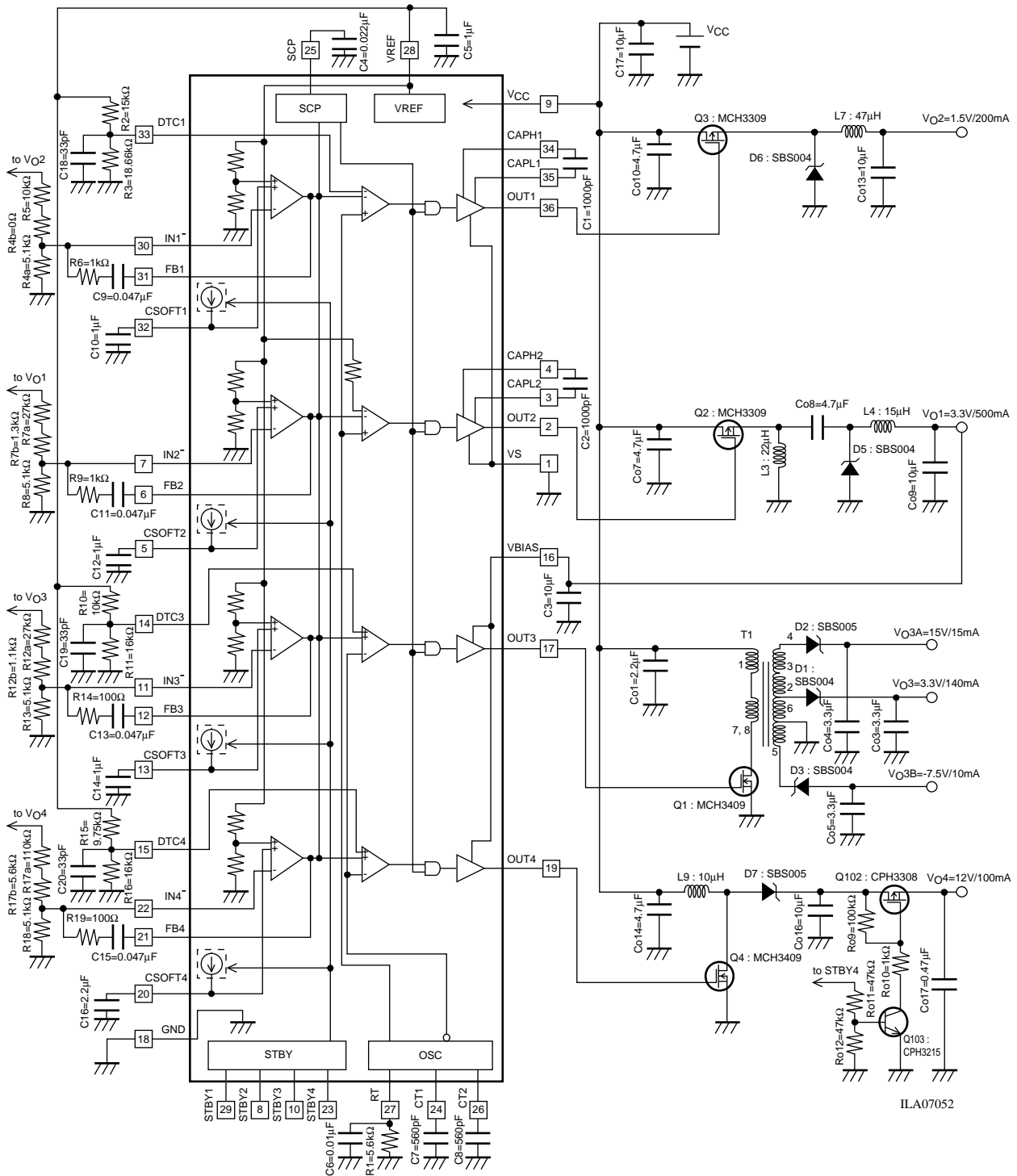


ILA07051

T1 = Sumida product
L4 = TDK product: RLF5018-220MR63
L7 = Toko product: 636CY-470M
L9 = Toko product: 636CY-100M

Application Circuit Examples 3

1-lithium ion battery (2.5V to 4.2V) configuration



T1 = Sumida product

L3 = TDK product: RLF5018-220MR63

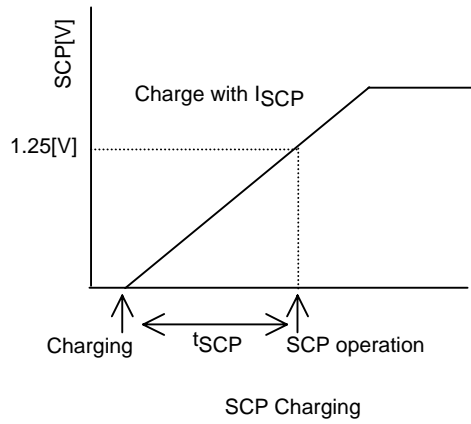
L4 = TDK product: RLF5018-150MR63

L7 = Toko product: 636CY-470M

L9 = Toko product: 636CY-100M

SCP Pin

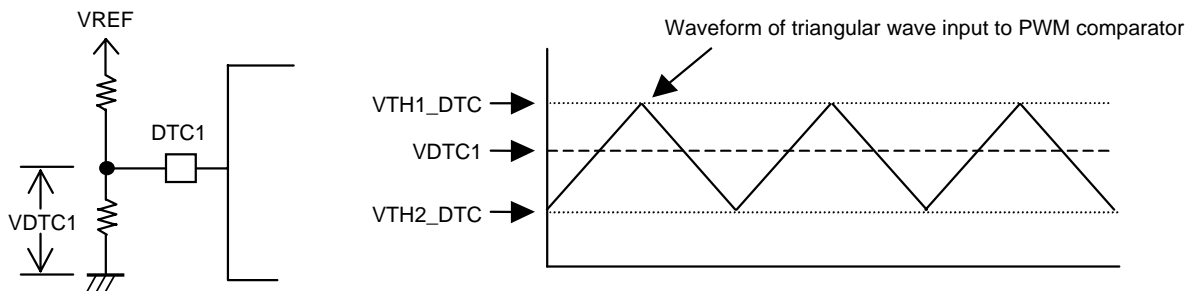
Charging of the SCP block starts when FB1 to FB4 are set to a low level due to a load shorting and the protection circuit is activated if the block does not reset itself within the preset time t_{SCP} (the protection circuit then turns off the whole OUT channels).



$$t_{SCP} = \frac{C_{SCP} \times V_{SCP}}{I_{SCP}} \quad [S]$$

Dead Time Setup

- The dead time of channel 1 can be set by the voltage at DTC1.



The duty cycle D1 is calculated as follows:

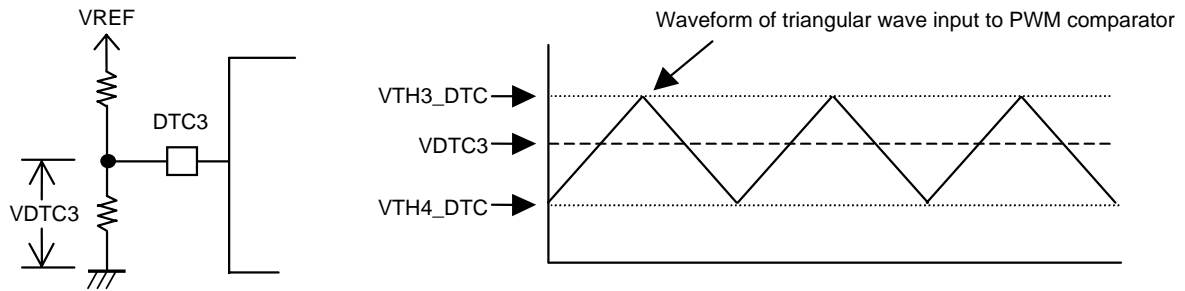
$$D1 = \frac{VDTC1 - V_{TH2_DTC}}{V_{TH1_DTC} - V_{TH2_DTC}} \times 100 [\%]$$

- Channel 2

The dead time of channel 2 is fixed internally and the setting duty is 100%.

- Channel 3

The dead time of channel 3 can be set by the voltage at DTC3.



The duty cycle D3 is calculated as follows:

$$D3 = \frac{V_{DTC3} - V_{TH4_DTC}}{V_{TH3_DTC} - V_{TH4_DTC}} \times 100 [\%]$$

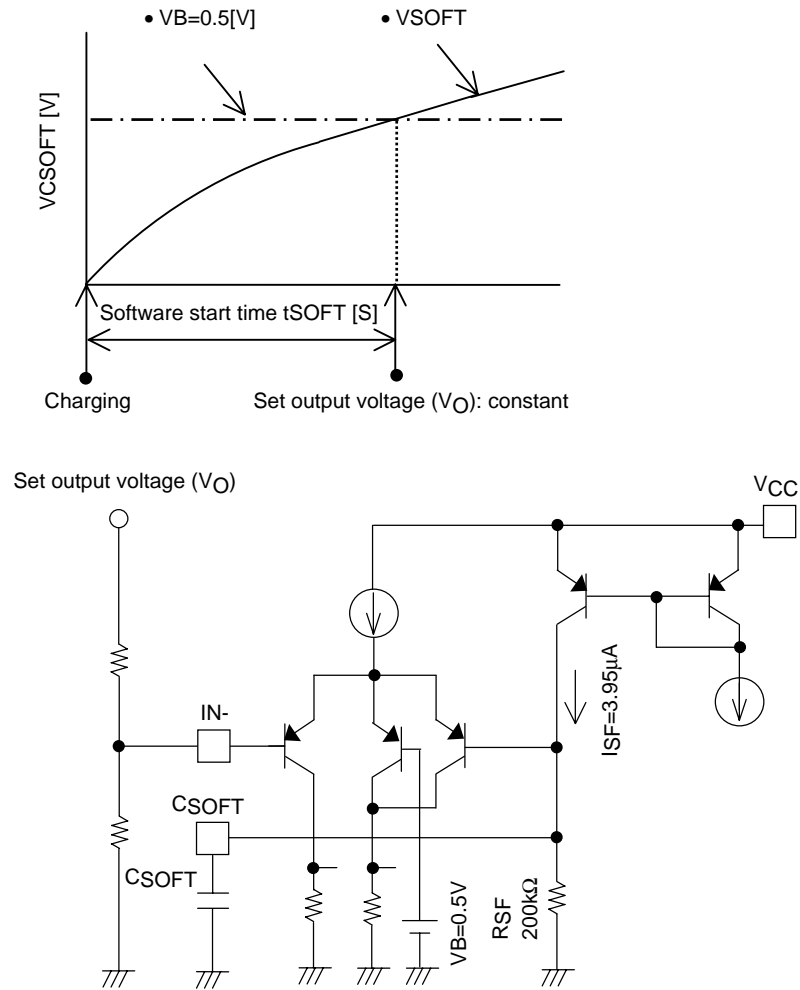
- Channel 4

The dead time of channel 4 can be set in the same manner as that of channel 3.

Procedure for Setting the Software Start Time

- Channel 1 (the procedure is the same for channels 2, 3, and 4.)

The software start time of channel 1 is set by the capacitance of the capacitor connected between pin CSOFT1 to CSOFT4 and GND.



$$t_{SOFT} = -C_{SOFT} \times R_{SF} \ln\left(1 - \frac{V_B}{R_{SF} \times I_{SF}}\right) [S]$$

* The formula is for channel 1.

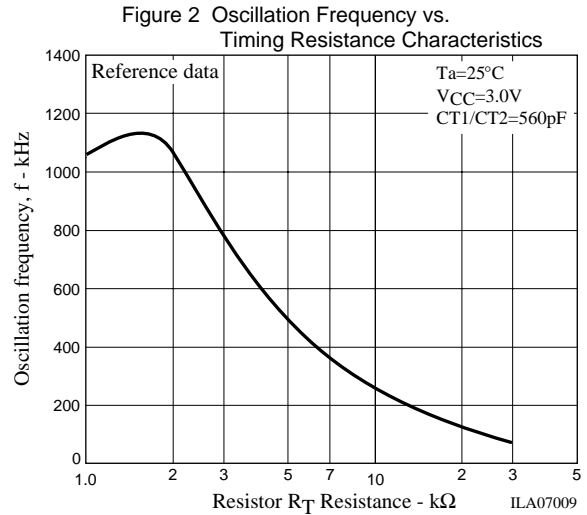
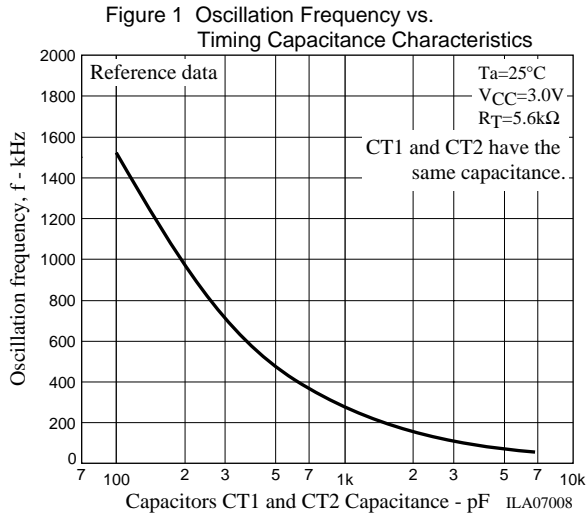
The software start time for channels 2 to 4 can be calculated in the same manner.

CT1 and CT2

The waveform of CT1 is 180 degrees out of phase with that of CT2. Their frequency cannot be set independently. The capacitance of the capacitors to be connected to pins CT1 and CT2 must be the same.

• Setting the oscillation frequency

- (1) The oscillation frequency of the oscillator can be set by selecting the capacitance of the capacitors connected to pins CT1 and CT2 (see Figure 1).
- (2) The oscillation frequency can also be determined by the resistance of the resistor connected to the RT pin (see Figure 2).

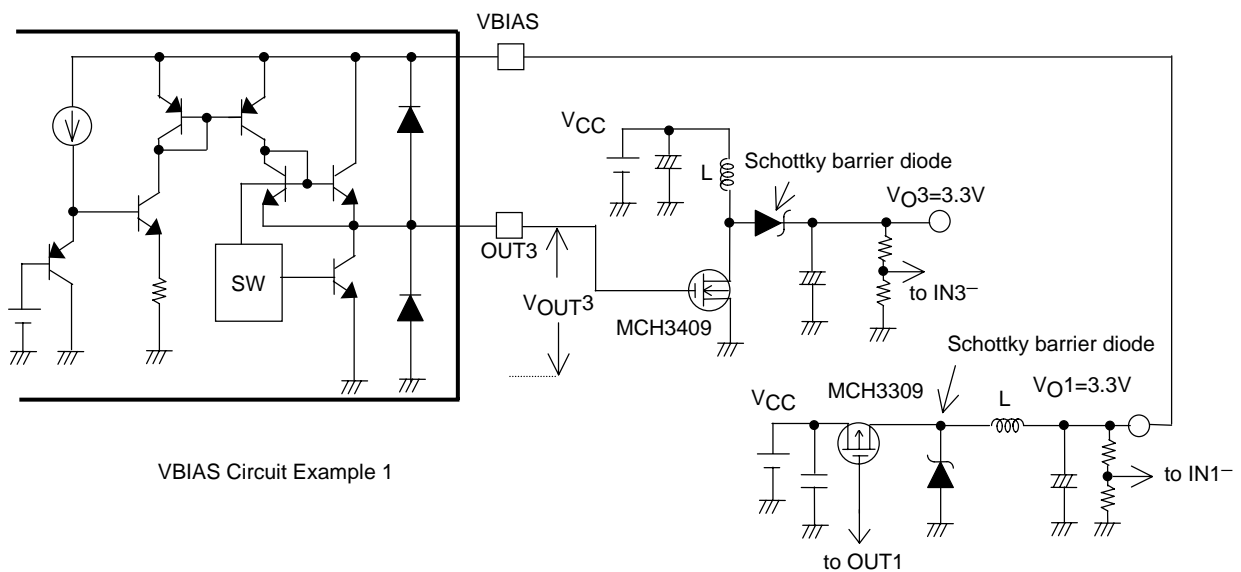


Sample Circuits

Sample Circuit That Makes Use of VBIAS (1)

This IC can be used to implement the circuit that is shown below since the power to the channels 3 and 4 output stages is supplied via VBIAS.

Apply V_{O1} that is dropped to 3.3V in channel 1 to VBIAS. A voltage of approx. VBIAS3-1 volt develops at V_{OUT3} , so that the IC can drive MOS transistors in a low-voltage environment like this sample circuit.

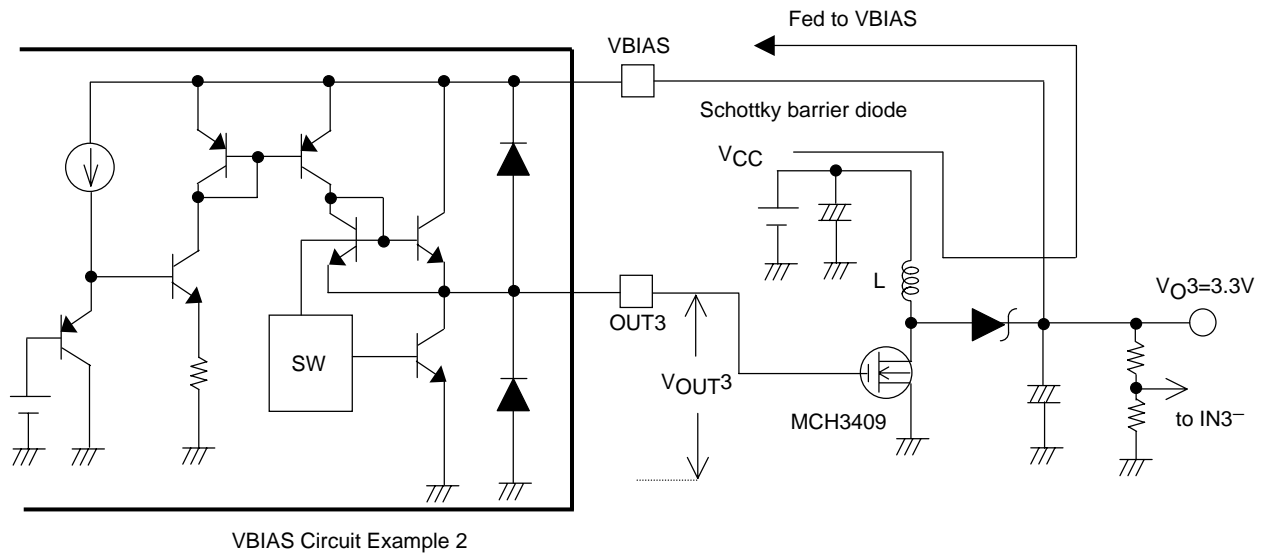


Sample Circuit That Makes Use of VBIAS (2)

This IC can be used to implement the circuit that is shown below since the power to the channels 3 and 4 output stages is supplied via VBIAS.

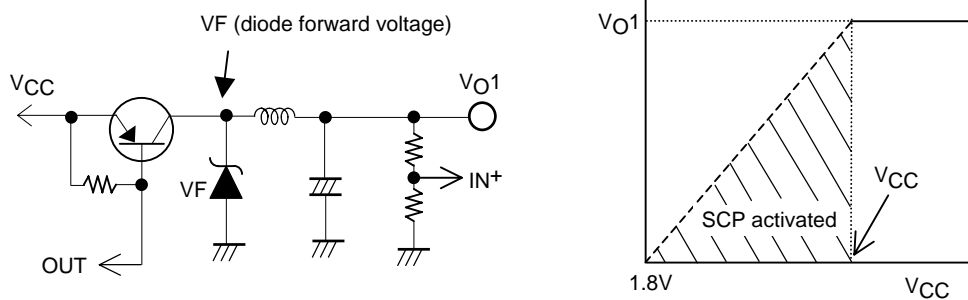
Apply the power voltage to VBIAS through the path that is made up of V_{CC} , L to Schottky diode (through path formation). Then feed the stabilized voltage V_{O3} that is raised to 3.3V in channel 3 to VBIAS.

A voltage of approx. $V_{BIAS3}-1$ volt develops at V_{OUT3} , so that the IC can drive MOS transistors in a low-voltage environment like this sample circuit.



Using the IC in a Step-down Circuit (CH1 and CH2)

The IC detects a short-circuit condition and activates the SCP when V_{CC} falls below the preset voltage V_O+V_F in such a step-down application as the one shown below.



Using the IC in a Step-up Circuit (CH3 and CH4)

In a step-up application like the one shown below, a through path consisting of V_{CC} , L, and D is formed when STBY is set off and a voltage normally remains present at V_O .

* Although the STBY off-time through path in the application circuit example is cut by a MOSFET, a voltage remains present at V_O after an SCP operation performed with STBY set on.

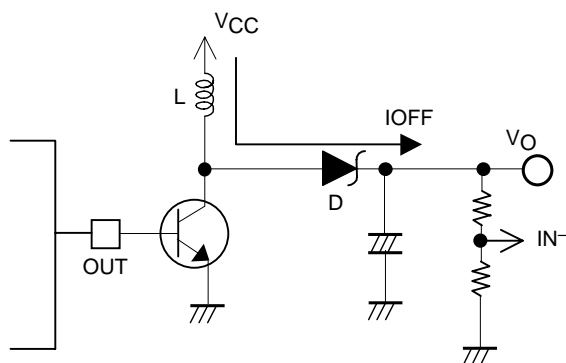


Figure Used with a Chopper Type Step-up Circuit

- Specifications of any and all SANYO Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- SANYO Semiconductor Co., Ltd. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all SANYO Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of SANYO Semiconductor Co., Ltd.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO Semiconductor product that you intend to use.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of April, 2006. Specifications and information herein are subject to change without notice.